



AO6420

N-Channel Enhancement Mode Field Effect Transistor

General Description

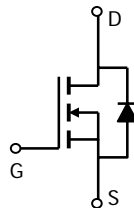
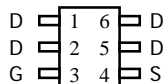
The AO6420 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications. *Standard Product AO6420 is Pb-free (meets ROHS & Sony 259 specifications).*

Features

- V_{DS} (V) = 60V
- I_D = 4.2A (V_{GS} = 10V)
- $R_{DS(ON)}$ < 60m Ω (V_{GS} = 10V)
- $R_{DS(ON)}$ < 75m Ω (V_{GS} = 4.5V)

R_g, C_{iss}, C_{oss}, C_{rss} Tested!

TSOP-6
Top View



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{A,F}	$T_A=25^\circ\text{C}$	4.2	A
	$T_A=70^\circ\text{C}$	3.4	
Pulsed Drain Current ^B	I_{DM}	20	
Power Dissipation	$T_A=25^\circ\text{C}$	2.00	W
	$T_A=70^\circ\text{C}$	1.28	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	$t \leq 10\text{s}$	48	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	74	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	35	40	$^\circ\text{C/W}$

N Channel Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	60			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1	μA
					5	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1	2.3	3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=4.2\text{A}$ $T_J=125^\circ\text{C}$		50	60	m Ω
				85		
				60	75	m Ω
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=4.2\text{A}$		13		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.78	1	V
I_S	Maximum Body-Diode Continuous Current				3	A
DYNAMIC PARAMETERS						
C_{ISS}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=30\text{V}$, $f=1\text{MHz}$		450	540	pF
C_{OSS}	Output Capacitance			60		pF
C_{RSS}	Reverse Transfer Capacitance			25		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1.65	2	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=30\text{V}$, $I_D=4.2\text{A}$		9.5	11.5	nC
$Q_g(4.5\text{V})$	Total Gate Charge			4.3	5.5	nC
Q_{gs}	Gate Source Charge			1.6		nC
Q_{gd}	Gate Drain Charge			2.2		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=30\text{V}$, $R_L=7\Omega$, $R_{GEN}=3\Omega$		5.1	7	ns
t_r	Turn-On Rise Time			2.6	4	ns
$t_{D(off)}$	Turn-Off DelayTime			15.9	20	ns
t_f	Turn-Off Fall Time			2	3	ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=4.2\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		25.1	35	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=4.2\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		28.7		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

F: The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

Rev0: Feb. 2007

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: N-CANNEL

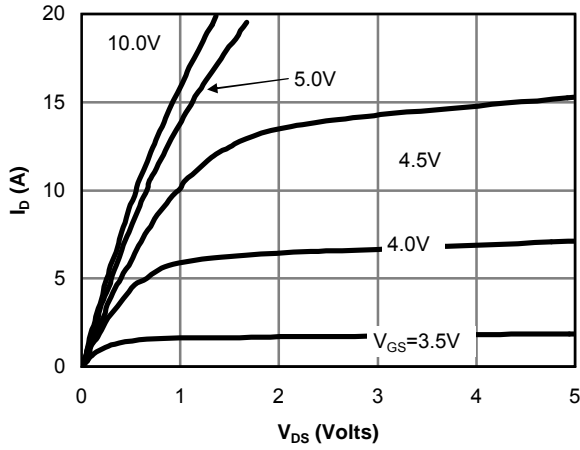


Fig 1: On-Region Characteristics

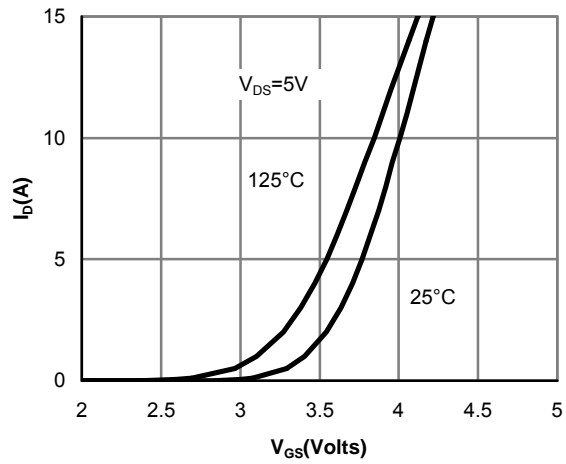


Figure 2: Transfer Characteristics

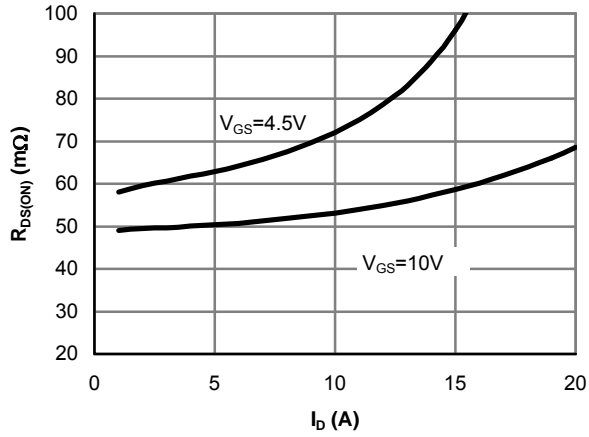


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

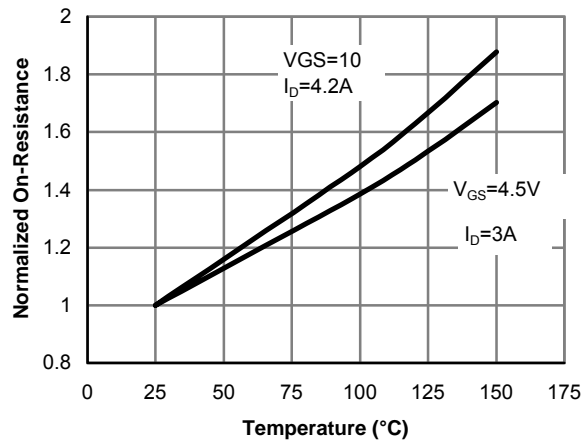


Figure 4: On-Resistance vs. Junction Temperature

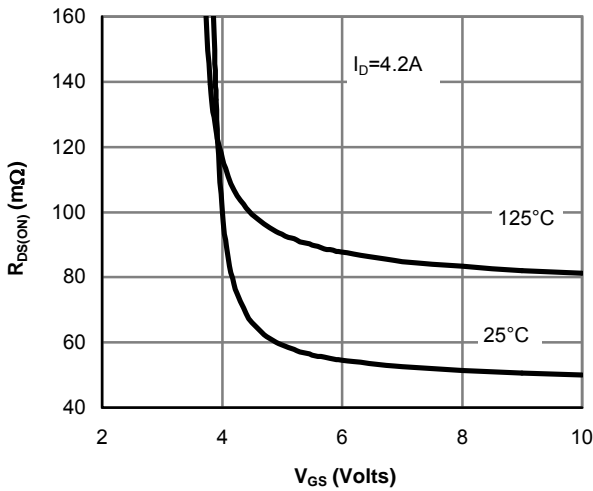


Figure 5: On-Resistance vs. Gate-Source Voltage

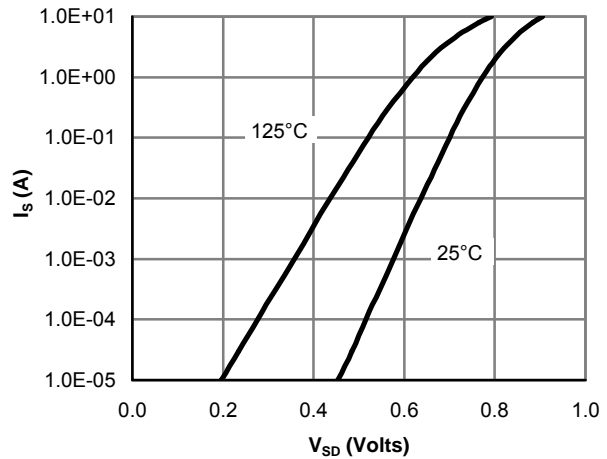


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: N-CHANNEL

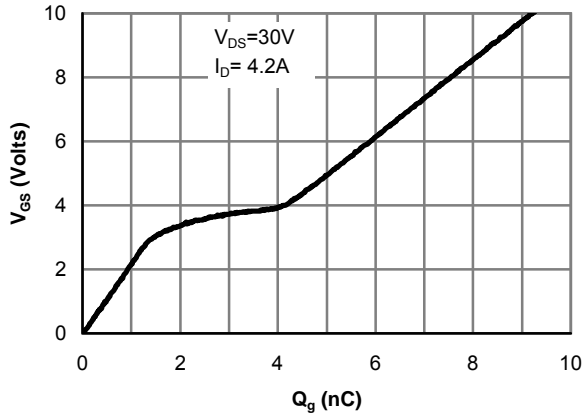


Figure 7: Gate-Charge Characteristics

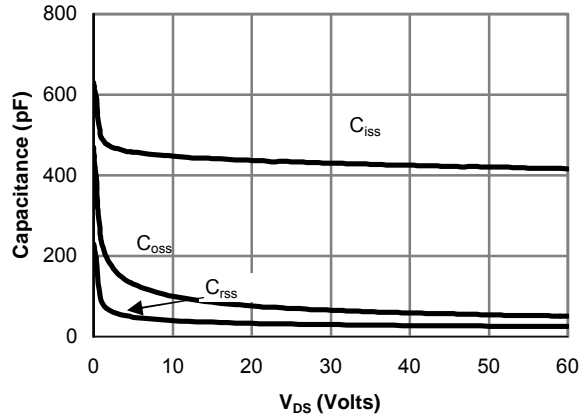


Figure 8: Capacitance Characteristics

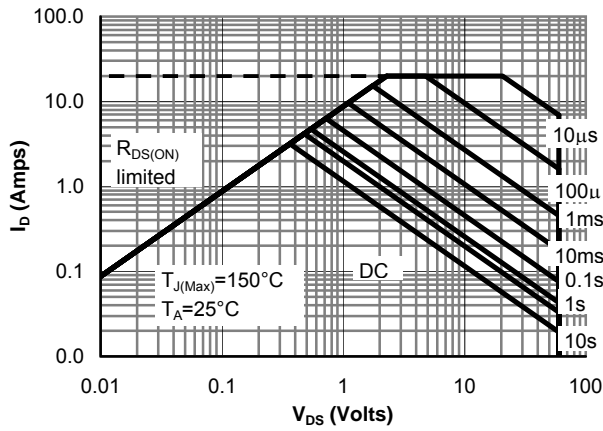


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

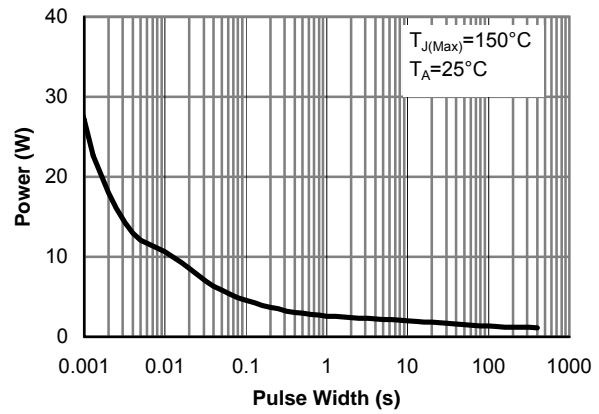


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

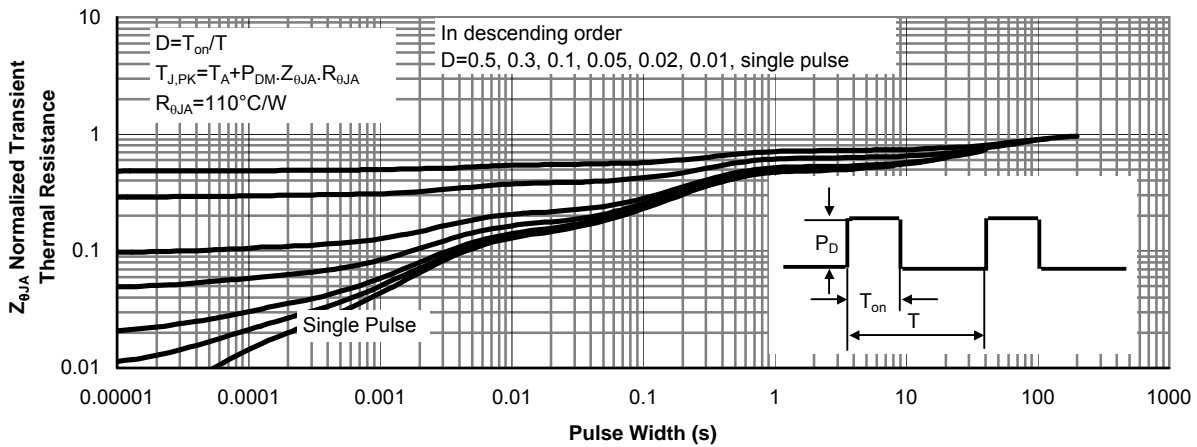


Figure 11: Normalized Maximum Transient Thermal Impedance